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03714121    \*\*Image available\*\*  
MANUFACTURE OF SEMICONDUCTOR DEVICE

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ABSTRACT

PURPOSE: To reduce cost, to improve producibility and to stabilize quality of a semiconductor device by cleaning a substrate surface while adding gas containing ozone to ammonia water solution.

CONSTITUTION: Mixture solution 104 of aqueous ammonia and pure water is heated by a heater 102 in a chemical solution tank 101. Gas containing ozone such as mixture gas 106 of ozone and oxygen is let out of a tube 105 which is introduced below the chemical tank 101 and is made to impinge on the surface of an Si substrate 103 for cleaning.

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